

	Claims Remaining After Amendment		Highest Number Previously Paid For	Present Extra	Rate	Fee
Total	48	-	42	6	(small entity) x 9 (others) x 18	\$108.00
Independent	6	-	6	0	(small entity) x 42 (others) x 84	\$0.00
Multiple Dependent (None)					(small entity) + 140 (others) + 280	\$0.00
TOTAL ADDITIONAL FEES						\$108.00

Applicants are enclosing the \$108.00 fee for the new claims. If any further fee should be due, please charge our deposit account 50/1039.

#### Conclusion

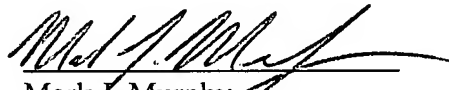
Applicants respectfully request allowance of this application.

Please charge our deposit account 50/1039 for any further fee due for this amendment.

Favorable reconsideration is earnestly solicited.

Respectfully submitted,

Date: January 14, 2003

  
 Mark J. Murphy  
 Registration No. 34,225

COOK, ALEX, McFARRON, MANZO,  
 CUMMINGS & MEHLER, LTD.  
 200 West Adams Street  
 Suite 2850  
 Chicago, Illinois 60606  
 (312) 236-8500

Marked-up copy of the amendments made herein:

**IN THE CLAIMS:**

Please amend the claims as follows:

36.(Twice Amended) A method of manufacturing a display device comprising the steps of:  
forming a thin film transistor over a substrate;  
forming a pixel electrode electrically connected to the thin film transistor;  
forming a body with a textured surface on the pixel electrode by a photolithography; and  
forming a light reflection film on the body with the textured surface [by one selected from the group consisting of a sputtering method, a coating method, and a vacuum evaporation method].

43.(Twice Amended) A method of manufacturing a display device comprising the steps of:  
forming a thin film transistor over a substrate;  
forming a pixel electrode electrically connected to the thin film transistor;  
forming a body with a textured surface on the pixel electrode by a photolithography;  
forming a light reflection film on the body with the textured surface [by one selected from the group consisting of a sputtering method, a coating method, and a vacuum evaporation method];  
and

flattening a surface of the light reflection film by a CMP process.

50.(Twice Amended) A method of manufacturing a display device comprising the steps of:  
forming a thin film transistor over a substrate;  
forming a pixel electrode electrically connected to the thin film transistor;  
forming a body with a textured surface on the pixel electrode by a photolithography; and  
forming a light reflection film on the body with the textured surface [by one selected from

the group consisting of a sputtering method, a coating method, and a vacuum evaporation method],  
wherein the light reflection film has a higher refractive index than the body with the textured surface.

57.(Twice Amended) A method of manufacturing a display device comprising the steps of:  
forming an insulated gate field effect transistor on a semiconductor substrate;  
forming a pixel electrode electrically connected to the insulated gate field effect transistor;  
forming a body with a textured surface on the pixel electrode by a photolithography; and  
forming a light reflection film on the body with the textured surface [by one selected from the group consisting of a sputtering method, a coating method, and a vacuum evaporation method].

64.(Twice Amended) A method of manufacturing a display device comprising the steps of:  
forming an insulated gate field effect transistor on a semiconductor substrate;  
forming a pixel electrode electrically connected to the insulated gate field effect transistor;  
forming a body with a textured surface on the pixel electrode by a photolithography;  
forming a light reflection film on the body with the textured surface [by one selected from the group consisting of a sputtering method, a coating method, and a vacuum evaporation method];  
and  
flattening a surface of the light reflection film by a CMP process.

71.(Twice Amended) A method of manufacturing a display device comprising the steps of:  
forming an insulated gate field effect transistor on a semiconductor substrate;  
forming a pixel electrode electrically connected to the insulated gate field effect transistor;  
forming a body with a textured surface on the pixel electrode by a photolithography; and

forming a light reflection film on the body with the textured surface [by one selected from the group consisting of a sputtering method, a coating method, and a vacuum evaporation method], wherein the light reflection film has a higher refractive index than the body with the textured surface.

Please add the following new claims:

78.(New) A method according to claim 36, wherein the light reflection film is formed by one selected from the group consisting of a sputtering method, a coating method, and a vacuum evaporation method.

79.(New) A method according to claim 43, wherein the light reflection film is formed by one selected from the group consisting of a sputtering method, a coating method, and a vacuum evaporation method.

80.(New) A method according to claim 50, wherein the light reflection film is formed by one selected from the group consisting of a sputtering method, a coating method, and a vacuum evaporation method.

81.(New) A method according to claim 57, wherein the light reflection film is formed by one selected from the group consisting of a sputtering method, a coating method, and a vacuum evaporation method.

82.(New) A method according to claim 64, wherein the light reflection film is formed by one selected from the group consisting of a sputtering method, a coating method, and a vacuum evaporation method.

83.(New) A method according to claim 71, wherein the light reflection film is formed by one selected from the group consisting of a sputtering method, a coating method, and a vacuum evaporation method.